

MMG200HB060B6EN

600V 200A IGBT Module

February 2017

Version 3

RoHS Compliant

PRODUCT FEATURE-8(ION)-10.4(S)25 TiD[(e224 1.08 re f BJ /5T2 1 T)-854534 0 85 Ti-106 687.4 8403 Tm 8 Tc 0 T<

APPLICATIONS

V_{GES}	Gate Emitter Voltage	$T_j=25$	600	V
			± 20	
I_C	DC Collector Current	$T_C=25$, $T_{Jmax}=175$	240	
		$T_C=60$, T		A

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IGBT-inverter

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

Unit

mA

mA

nA

μC

nF

pF

ns

ns

ns

ns

ns

ns

ns

ns

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NTC CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Resistance $T_C=25$		5		K K
					Unit
					V
					Nm
					Nm
					g

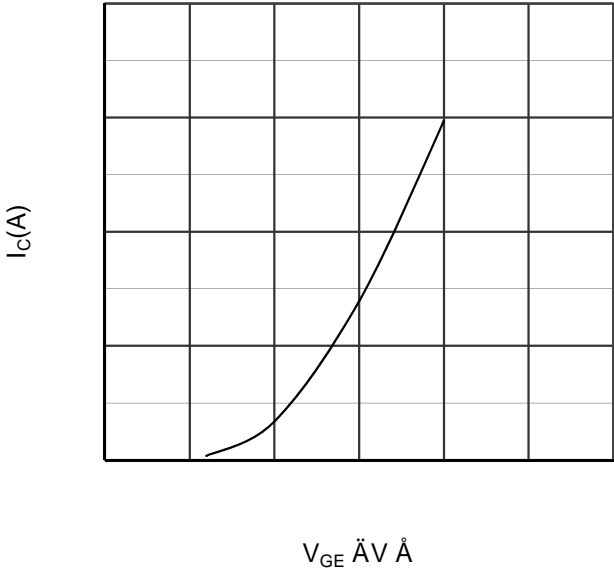


Figure 3. Typical Transfer characteristics IGBT-inverter

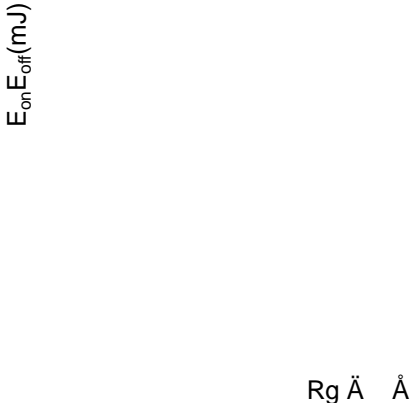


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

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$I_F(A)$

$E_{REC}(mJ)$

$V_F(V)$

Figure 14. Circuit Diagram

Dimensions in (mm)
Figure 15. Package Outline